

Title (en)
SEMICONDUCTOR DEVICE AND METHOD FOR MANUFACTURING SAME

Title (de)
HALBLEITERBAUELEMENT UND VERFAHREN ZU SEINER HERSTELLUNG

Title (fr)
DISPOSITIF SEMI-CONDUCTEUR ET SON PROCEDE DE FABRICATION

Publication
EP 1887631 A4 20080827 (EN)

Application
EP 06731512 A 20060410

Priority
• JP 2006307565 W 20060410
• JP 2005164301 A 20050603

Abstract (en)
[origin: EP1887631A1] The semiconductor device includes a semiconductor substrate, a plurality of source regions formed in a stripe shape on the semiconductor substrate, a plurality of gate electrodes formed in a stripe shape between a plurality of the stripe shaped source regions on the semiconductor substrate, an insulating film for covering the source regions and the gate electrodes, the insulating film including a contact hole for partly exposing the source regions in a part of a predetermined region with respect to a longitudinal direction of the source regions; and a source electrode formed on the insulating film and electrically connected to the source region via the contact hole.

IPC 8 full level
H01L 29/78 (2006.01); **H01L 21/336** (2006.01); **H01L 29/06** (2006.01); **H01L 29/423** (2006.01); **H01L 29/10** (2006.01); **H01L 29/45** (2006.01); **H01L 29/49** (2006.01)

CPC (source: EP KR US)
H01L 29/0696 (2013.01 - EP KR US); **H01L 29/0869** (2013.01 - EP US); **H01L 29/1095** (2013.01 - EP KR US); **H01L 29/41741** (2013.01 - US); **H01L 29/4238** (2013.01 - EP KR US); **H01L 29/456** (2013.01 - EP KR US); **H01L 29/4933** (2013.01 - KR); **H01L 29/665** (2013.01 - EP KR US); **H01L 29/66712** (2013.01 - US); **H01L 29/66719** (2013.01 - EP KR US); **H01L 29/7802** (2013.01 - EP KR US); **H01L 29/4933** (2013.01 - EP US)

Citation (search report)
• [X] US 5844277 A 19981201 - HSHIEH FWU-IUAN [US], et al
• [X] US 4677452 A 19870630 - ZOMMER NATHAN [US]
• [A] EP 0393949 A1 19901024 - GEN ELECTRIC [US]
• See references of WO 2006129423A1

Designated contracting state (EPC)
DE FR GB

DOCDB simple family (publication)
EP 1887631 A1 20080213; **EP 1887631 A4 20080827**; CN 101176210 A 20080507; JP 2006339516 A 20061214; KR 20080011382 A 20080204; TW 200705663 A 20070201; US 2009121293 A1 20090514; US 2016064542 A1 20160303; US 9202891 B2 20151201; US 9837525 B2 20171205; WO 2006129423 A1 20061207

DOCDB simple family (application)
EP 06731512 A 20060410; CN 200680016084 A 20060410; JP 2005164301 A 20050603; JP 2006307565 W 20060410; KR 20077025321 A 20071031; TW 95113540 A 20060414; US 201514937835 A 20151110; US 88710206 A 20060410